# Intermediate ground states of hydrogen in LaNiO<sub>2</sub>: A first-principles study

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Infinite-layer nickelate superconductors  $RNiO_2$  (R = La, Nd, Pr) are synthesized via chemical reduction using the CaH<sub>2</sub> agent, and the unintentional introduction of H dopant during the reduction process may affect  $RNiO_2$  quality and ultimately determine their electronic properties. However, the ground-state configurations and electronic structures of  $RNiO_2$  under varying H concentrations ( $\delta$ ) remain unclear. In this work, we employ the cluster-expansion method and first-principles calculations to examine the intermediate ground-state structures, electronic structures, and magnetic properties of LaNiO<sub>2</sub>H<sub> $\delta$ </sub> ( $0 < \delta < 1$ ). Interestingly, our results show that H always occupies apical oxygen vacancies, forming ordered H-Ni-H chains along the out-of-plane direction but with different  $\delta$ -dependent patterns along the in-plane direction. Notably, the interstitial *s*-like orbital in the LaNiO<sub>2</sub> host is annihilated by H and the filling of the Ni 3*d* bands, especially the  $3d_{x^2-y^2}$  and  $3d_{z^2}$  orbitals, is greatly altered. With H doping, both enhanced magnetic stability of *G*-type antiferromagnetic states and simultaneous metal-to-insulator transition occur. Our study demonstrates the remarkable doping impact of H in LaNiO<sub>2</sub>, allowing us to gain deeper insight into the structure and superconductivity of infinite-layer nickelates.

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### I. INTRODUCTION

The infinite-layer nickelate superconductors represent new platforms for the study of unconventional superconductivity. Observed in NdNiO<sub>2</sub> [1-3], unconventional superconducting behaviors have also been observed in PrNiO<sub>2</sub> [4,5], LaNiO<sub>2</sub> [6], etc. [7]. This leads to comprehensive studies in nickelate superconductors  $RNiO_2$  (R = La, Nd, Pr) [8–24]. Furthermore, a successive detection of magnetic fluctuations [25,26] and charge density waves [27,28] within the nickelate family has raised the intriguing question regarding their similarity to cuprates. However, due to challenges in reduction synthesis by CaH<sub>2</sub> agents, only a few groups worldwide have reproduced superconducting behaviors in nickelates [1,29]. Very recently, Ding et al. demonstrated that unintentional H doping may commonly present in epitaxial infinite-layer nickelates. Furthermore, they found that the insertion of H atoms may modulate orbital hybridization, thereby exerting control over the overall superconducting phase diagram of the samples [30].

Theoretical studies of  $RNiO_2$  indicate that H atoms have noticeable influences on the Fermi surfaces, electronic correlations, and magnetic stability of these systems [30–32]. However, these studies are all based on several artificial H concentrations ( $\delta$ ) in *P4/mmm* supercells [30–32]. Thus, it is doubtful whether the conclusions obtained from these artificial structures are reliable. In a real doped system, homogeneous intermediate ground states can exist for specific  $\delta$ , while at any arbitrary  $\delta$  inhomogeneous phases may also exist in between these intermediate ground states [33,34]. To obtain a comprehensive understanding of the physical properties of a doped system, it is necessary to investigate numerous atomic configurations to identify the possible intermediate ground states. However, it should be noted that such extensive research on  $RNiO_2$  is currently lacking.

To determine the multiple intermediate configurations in  $RNiO_2H_{\delta}$  (0 <  $\delta$  < 1), the cluster expansion (CE) method, commonly adopted in binary alloys [35–37], can be used to search for the intermediate ground states in our study, considering "vacancy" and H atom as two kinds of alloying atoms. With possible intermediate ground states of infinite-layer nickelates, we may yield a deeper understanding of superconductivity in  $RNiO_2H_{\delta}$  by examining the relationship between H doping and the electronic properties of  $RNiO_2$ .

In this study, a combination of the CE method and first-principles calculations has been performed to obtain intermediate configurations. In addition to LaNiO<sub>2</sub> and LaNiO<sub>2</sub>H, four intermediate ground states with different  $\delta$ ( $\delta = 0.33$ , 0.5, 0.67, 0.83) are found in LaNiO<sub>2</sub>H<sub> $\delta$ </sub>. Interestingly, there are two basic rules for the stable configurations of H in LaNiO<sub>2</sub>H<sub> $\delta$ </sub>, that is, (i) H atoms occupy the apical oxygen vacancies, forming ordered H-Ni-H chains along the out-ofplane direction, and (ii) H can exhibit different  $\delta$ -dependent ordered in-plane patterns. As for electronic structure, the insertion of H results in two distinct local environments of Ni (NiO<sub>4</sub> and NiO<sub>4</sub>H<sub>2</sub>) and significantly alters the orbital

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fillings of Ni 3*d* orbitals. Consequently, it modulates the orbital polarization that is related to the superconductivity in LaNiO<sub>2</sub>H<sub> $\delta$ </sub>. Importantly, in the *G*-type antiferromagnetic (AFM-*G*) states which exhibit the lowest energy, the spin-polarization energy increases with  $\delta$ , accompanied by an unexpected metal-to-insulator transition. Our study provides insight into the structural and electronic structure properties of nickelates, specifically focusing on the effects of more realistic H doping conditions.

### **II. METHOD**

The density functional theory (DFT) calculations are performed within the projector augmented wave (PAW) method [38] and the Perdew-Burke-Ernzerhof (PBE) functional [39], as implemented in Vienna Ab initio Simulation Package (VASP) [40]. The kinetic-energy cutoff for the plane-wave basis is set to 520 eV and the force on each atom is less than  $1 \times 10^{-3}$  eV Å<sup>-1</sup> to obtain a converged total energy. We apply the CE method established in alloy theory [35] to explore the LaNiO<sub>2</sub>H<sub> $\delta$ </sub> system. To search for intermediate ground-state structures at different H concentrations, we have utilized the Alloy-Theoretic Automated Toolkit (ATAT) code [41] and all atoms and lattice vectors are fully relaxed. ATAT randomly generates almost all possible 780 nonequivalent structures with each unit cell containing a maximum of 36 atoms, of which the formation energies  $(E_f)$  of 91 structures are calculated at the DFT level and subsequently used in the fitting process. The cross-validation score is set to 0.01 eV, which ensures the convergence of the CE fit in the calculation.

In addition, the DFT + U method is adopted [42] in all calculations, and U on Ni 3d is set to 5 eV unless specified, in agreement with previous reports [43]. For calculations exploring intermediate ground-state structures, spin-polarized calculation is not utilized. For the magnetic calculations at each H concentration ( $\delta = 0, 0.33, 0.5, 0.67, 0.83, 1$ ), spin-polarized calculation is employed based on the nonmagnetic structures and supercells are used to accommodate possible magnetic configurations, and three possible spin configurations are calculated in each H concentration, i.e., ferromagnetic (FM), C-type antiferromagnetic (AFM-C, antiferromagnetic arrangement for in-plane Ni, and ferromagnetic arrangement for out of plane Ni), and AFM-G (both in-plane and out-of-plane Ni are antiferromagnetic arrangements). To compare the effect of inserted H atoms on electronic structures, all band structures calculated using the supercells are unfolded to the unit cell of LaNiO2. The band unfolding is done by projecting supercell wave functions onto the primitive cell wave functions to determine the weights of primitive cell wave functions, enabling the calculation of the effective band structure for doped systems [44–46].

#### **III. RESULTS AND DISCUSSION**

## A. Intermediate ground-state structures of $LaNiO_2H_\delta$

To explore the intermediate ground-state structures at various  $\delta$ , we treat LaNiO<sub>2</sub>H<sub> $\delta$ </sub> as an alloy system and employ the CE method [35,41]. The basic idea of CE is to expand the energy of LaNiO<sub>2</sub>H<sub> $\delta$ </sub> into energetic contributions of cluster configurations based on a generalized (single atoms, pairs,

TABLE I. Structure parameters (lattice constant and angle) of the ground-state structures of LaNiO<sub>2</sub>H<sub> $\delta$ </sub> at  $\delta = 0$ , 0.33, 0.5, 0.67, 0.83, and 1.

δ	0	0.33	0.5	0.67	0.83	1
$a(\text{\AA})$	3.905	10.966	10.983	8.681	10.965	3.905
b(Å)	3.905	8.619	8.687	8.681	8.700	3.905
c(Å)	3.450	3.461	3.460	3.469	3.478	3.450
$\alpha(^{\circ})$	90	90	90	90	90	90
$\beta(^{\circ})$	90	90	90	90	90	90
γ(°)	90	107.523	108.452	143.196	108.433	90

triples, etc.) Ising Hamiltonian:

$$E_{(\sigma)} = J_0 + \sum_i J_i \hat{s}_i(\sigma) + \sum_{i < j} J_{ij} \hat{s}_i(\sigma) \hat{s}_j(\sigma)$$
$$+ \sum_{i < j < k} J_{ijk} \hat{s}_i(\sigma) \hat{s}_j(\sigma) \hat{s}_k(\sigma) + \dots$$
(1)

The indexes *i*, *j*, and *k* run over all occupation positions, and  $S_{\rm m}(\sigma)$  takes on a value of either +1 or -1, indicating an occupied H and empty site, respectively. By employing the CE method, the energy  $E_{(\sigma)}$  of any LaNiO<sub>2</sub>H<sub> $\delta$ </sub> alloy can be calculated by selecting a suitable value of  $J_{\alpha}$ , which can be fitted from the DFT-calculated total energy of related structures [47].

The  $E_f$  of LaNiO<sub>2</sub>H<sub> $\delta$ </sub> is defined as

$$E_f = E[\text{LaNiO}_2\text{H}_{\delta}] - (1 - \delta)E(\text{LaNiO}_2) - \delta E(\text{LaNiO}_2\text{H}),$$
(2)

where  $E(\text{LaNiO}_2)$  and  $E(\text{LaNiO}_2\text{H})$  represent the energy of the LaNiO<sub>2</sub> and LaNiO<sub>2</sub>H, respectively. The resulting convex hull diagram is shown in Fig. 1(a). The structures on the convex hull [red line in Fig. 1(a)] represent thermodynamically stable structures, while those above the convex hull correspond to metastable structures. Four intermediate ground states are determined with  $\delta = 0.33, 0.5, 0.67, \text{ and } 0.83$  where the corresponding structures are given in Figs. 1(b)–1(g), i.e., LaNiO<sub>2</sub> ( $D_{4h}$  symmetry), LaNiO<sub>2</sub>H<sub>0.33</sub> ( $C_s$  symmetry), LaNiO<sub>2</sub>H<sub>0.5</sub> ( $C_s$  symmetry), LaNiO<sub>2</sub>H<sub>0.67</sub> ( $D_{2h}$  symmetry), LaNiO<sub>2</sub>H<sub>0.83</sub> ( $C_{2h}$  symmetry), and LaNiO<sub>2</sub>H ( $D_{4h}$  symmetry). The corresponding lattice parameters are shown in Table I.

As shown in Fig. 1, we find that the insertion H located at the position of the apical oxygen vacancy site has the lowest energy. Interestingly, the H atoms in these four intermediate ground states show two universal features: (1) Along the out-of-plane direction, H atoms occupy the apical oxygen vacancies and form ordered H-Ni-H chains with strongly bonded Ni-3 $d_{r^2}$  orbital, consistent with previous studies [30–32]. We note that the formation of an ordered H-Ni-H chain is not caused by periodic boundary conditions, but is the consequence in terms of total energy. The formation of H-Ni-H chains is independent of the  $\delta$ . (2) Along the in-plane direction, H atoms form different patterns. As shown in the lower panel of Figs. 1(c)–1(f), when  $\delta = 0.33$ , H atoms prefer a diagonal arrangement; when  $\delta > 0.33$ , H atoms are not diagonally arranged. Overall, our study indicates that H could form ordered states in LaNiO<sub>2</sub>, instead of a random distribution. For an arbitrary  $\delta$ , ideally, LaNiO<sub>2</sub>H<sub> $\delta$ </sub> may separate into a linear combination of its neighboring intermediate ground states.



FIG. 1. Geometric structures of LaNiO<sub>2</sub>H<sub> $\delta$ </sub>. (a) The calculated  $E_f$  with the corresponding CE fits as a function of H concentration  $\delta$ . Panels (b)–(g) are ground-state structures at  $\delta = 0$ , 0.67, 0.33, 0.5, 0.83, and 1, respectively. The upper and lower panels correspond to the side and top views, respectively. The gray-solid line represents the primitive cell. The green, gray, red, and pink balls represent lanthanum (La), nickel (Ni), oxygen (O), and hydrogen (H) atoms, respectively. The pink dashed line represents a diagonal site.

### B. Electronic structures of LaNiO<sub>2</sub>H<sub>δ</sub>

To further investigate the evolution of electronic properties with  $\delta$ , we draw the band structures and density of states (DOS) for these intermediate ground states with five major orbitals projections [ La-5 $d_{z^2}$ , La-5 $d_{xv}$ , Ni-3 $d_{z^2}$ , Ni-3 $d_{x^2-v^2}$ , and interstitial s (IIs) orbital]. As shown in Fig. 2, except for LaNiO<sub>2</sub>H, all structures have clear IIs states located at the apical oxygen vacancy [8,10,30]. With increasing  $\delta$ , the intensity of this IIs state is reduced and finally annihilated while its position moves towards higher energy. Interestingly, the band structure along the Z-R-A-Z line and DOS show important features of the evolution of 3d orbitals: (i) the band dispersion of  $3d_{x^2-y^2}$  is hardly changed, while the energy level shifts slightly downward with increasing  $\delta$ , and (ii) the band dispersion of  $3d_{7^2}$  is changed greatly and the energy level moves close to the Fermi level  $(E_{\rm F})$ . On the other hand, the band dispersion and orbital occupation of La 5d orbitals, with a small proportion around  $E_{\rm F}$ , are barely changed.

In addition, the insertion of H leads to two different local environments of Ni. One Ni is at the face center of the NiO<sub>4</sub> square (denoted as Ni1), and the other is at the body center of the NiO<sub>4</sub>H<sub>2</sub> octahedron (denoted as Ni2). The DOS for these two Ni atoms is drawn separately, showing different 3*d* orbitals filling. For Ni1,  $3d_{z^2}$  is almost fully occupied, while  $3d_{x^2-y^2}$  is half filled. For Ni2, because of the strong bond with H 1s orbital,  $3d_{z^2}$  is pushed up towards  $E_F$ . Meanwhile, the occupation of  $3d_{x^2-y^2}$  is increased in Ni2 compared with Ni1. For any intermediate ground-state structure, the DOS of 3d in the NiO<sub>4</sub> environment is similar to that in LaNiO<sub>2</sub> and 3d orbitals in the NiO<sub>4</sub>H<sub>2</sub> environment are similar to that in LaNiO<sub>2</sub>H, indicating the relatively local effect caused by the H insertion.

To qualitatively evaluate the filling variation of 3d orbital with  $\delta$ , we integrate the DOS of total Ni-3d,  $3d_{x^2-y^2}$ , and  $3d_{z^2}$ orbitals under  $E_{\rm F}$ , respectively. For the total 3d, as shown in Fig. 3(a), in LaNiO<sub>2</sub> the total 3d filling is 8.82e and the corresponding valence of Ni is +1.18e, which is very close to the  $d^9$  configuration and in agreement with previous DFT or dynamical mean-field theory (DMFT) studies [48,49]. With an increasing  $\delta$ , the 3*d* filling decreases slightly and the orbital filling is decreased to 8.67 e in LaNiO<sub>2</sub>H. This may be due to both the hole doping effect induced by H and the compensation effect of holes to IIs electrons [30]. For the  $3d_{r^2-v^2}$  orbital, as shown in Fig. 3(b), the orbital filling of Ni2 is increased by  $\sim 0.3 e$  compared with Ni1 under different  $\delta$ . For the  $3d_{7^2}$  orbital, strong bonding is formed between the symmetry-matched Ni  $3d_{7^2}$  and H 1s orbitals at the Ni2 site, causing the antibonding states pushed to higher energy and close to the  $E_{\rm F}$  while the bonding states are down to an even lower energy level. Therefore, it is expected that the orbital



FIG. 2. Unfolded band structures and density of states (DOS) with orbital projections for LaNiO<sub>2</sub>H<sub> $\delta$ </sub> ( $\delta = 0, 0.33, 0.5, 0.67, 0.83, 1$ ). The solid (dashed) lines in DOS are for the 3*d* orbitals in the NiO<sub>4</sub> (NiO<sub>4</sub>H<sub>2</sub>) environment. The DOS of IIs is enlarged by five times for the eyes. The *E*<sub>F</sub> is set to zero.

filling of  $3d_{z^2}$  at Ni2 site is smaller than that at Ni1 site, opposite to  $3d_{x^2-y^2}$ . Indeed, as shown in Fig. 3(c), the  $3d_{z^2}$ filling of Ni2 is reduced by ~ 0.2 *e* compared to Ni1. This reduction is also identified from the band structures and DOS in Fig. 2: the projection of  $3d_{z^2}$  around  $E_F$  increases more as  $\delta$  increases. Therefore, considering the two opposite trends of  $3d_{z^2}$  and  $3d_{x^2-y^2}$  filling at Ni1 and Ni2 sites, the total 3dfilling is less sensitive to  $\delta$  in NiO<sub>4</sub> and NiO<sub>4</sub>H<sub>2</sub> environments (~0.1 *e*), as shown in Fig. 3(a). That is, the insertion of H mainly reduces the occupation of the IIs orbital, leaving the occupation of the 3*d* orbitals hardly changed.

In addition, to better describe the electronic structures of transition metal oxides, electron-electron interaction is always taken into account by the Hubbard *U* formula. In infinite-layer nickelates, the value of *U* for Ni is set to 3–6 eV in DFT calculations [13,17,29,50]. To demonstrate that the electronic structures with different  $\delta$  are insensitive to *U*, the band structure and DOS of LaNiO<sub>2</sub>, LaNiO<sub>2</sub>H<sub>0.5</sub>, and LaNiO<sub>2</sub>H are also calculated with U = 3 eV, as shown in Fig. 4.

The electronic structures of U = 3 and 5 eV are thoroughly compared (Figs. 2 and 4). First, the bands with U = 3 eV shift slightly upward more than U = 5 eV, and the van Hove singularity with U = 3 eV is closer to  $E_F$  at the *R* point. Second, with U = 3 eV, the electronic pocket at the  $\Gamma$  point becomes smaller as a result of slight difference in Coulomb repulsion caused by *U*. Furthermore, despite different *U*, the evolution of orbital occupation and DOS with  $\delta$  is consistent. Therefore, qualitatively our main conclusions are not influenced by the variation of *U*.

#### C. Magnetic properties of LaNiO<sub>2</sub>H<sub>δ</sub>

Despite lacking long-range magnetic order [51,52], recent experiments have revealed short-range antiferromagnetic interactions in  $RNiO_2$  [16,26]. So far, theoretical research of magnetic interaction behaviors [14,17,19,21,24,53–56] has focused on  $RNiO_2$  systems without H doping while whether



FIG. 3. Orbital fillings as a function of H concentration  $\delta$  in LaNiO<sub>2</sub>H<sub> $\delta$ </sub>. (a)–(c) Orbital fillings of total 3*d*, 3*d*<sub>*z*<sup>2</sup>-*y*<sup>2</sup></sub>, and 3*d*<sub>*z*<sup>2</sup></sub> orbitals. Open and filled symbols represent the orbital fillings of Ni in Ni1 (NiO<sub>4</sub> environment) and Ni2 (NiO<sub>4</sub>H<sub>2</sub> environment), respectively. The inset structures in (a) and (b) correspond to the local environments of Ni in Ni1 and Ni2, respectively.



FIG. 4. Electronic structure of  $LaNiO_2H_\delta$  with Hubbard U = 3 eV. (a)–(c) Unfolded band structures and DOS with orbital projections for  $LaNiO_2$ ,  $LaNiO_2H_{0.5}$ , and  $LaNiO_2H$ . The solid (dashed) lines in DOS are for the 3*d* orbitals in the NiO<sub>4</sub> (NiO<sub>4</sub>H<sub>2</sub>) environment. The DOS of IIs is enlarged by five times for the eyes. The  $E_F$  is set to zero.

the magnetic interactions will be influenced by H is still an open question.

For each  $\delta$ , to explore the magnetic properties in LaNiO<sub>2</sub>H<sub> $\delta$ </sub> we have calculated the total energy of nonmagnetic (NM), FM, AFM-C, and AFM-G states, and the results are shown in Fig. 5(a), where the energy of the AFM-G configuration is set to zero as a reference. For LaNiO<sub>2</sub>, the energies of different magnetic orders are comparable. The energies of AFM-G and FM configurations are pretty close, and both are only  $\sim$ 3 meV/Ni higher than the AFM-C configuration, indicating that AFM-C is the ground state, consistent with the previous theoretical study [57]. Interestingly, with  $\delta$  increases, the energy differences between different magnetic configurations also increase, while the magnetic ground-state configuration is stabilized as the AFM-G state. Therefore, H plays an important role to distinguish the different magnetic groundstate configurations. For example, with  $\delta = 0.33$ , AFM-G is  $\sim$ 60 meV/Ni lower than AFM-C and FM. As  $\delta$  increases from 0.5 to 1, the AFM-G is more stable, whereas the energy of AFM-C becomes much lower than FM, indicating stronger antiferromagnetic interaction with increasing  $\delta$ . Figure 5(b) shows the total DOS of three magnetic configurations with

 $\delta = 0, 0.5, \text{ and } 1$ , respectively, as an illustration of the effect of H doping on magnetic properties. For FM, the systems are all metal despite different  $\delta$ . For AFM-*C* and AFM-*G*, there is a metal-insulator phase transition under H doping. LaNiO<sub>2</sub> is a metal phase, which transforms into an insulator phase in LaNiO<sub>2</sub>H. Besides, the band gap of the H-doped AFM-*G* is more prominent than that of the AFM-*C*.

The above discussion shows that, in LaNiO<sub>2</sub>H<sub> $\delta$ </sub>, as H concentration increases, AFM-*G* is the dominant magnetic ground state. Therefore, focusing on the metal-insulator transition (under the DFT + *U* level calculations) in the AFM-*G* state, we have analyzed the evolution of band structures and DOS with increasing  $\delta$ , as shown in Fig. 6. First of all, the orbitals near  $E_{\rm F}$  are mainly IIs,  $3d_{x^2-y^2}$  and  $3d_{z^2}$  in LaNiO<sub>2</sub>, as shown in Fig. 6(a). With the increase of  $\delta$ , the IIs orbital is gradually annihilated and the coupling between IIs and  $3d_{z^2}$  is weakened, leading to the opening of the band gap. In addition, the band gap becomes larger with increasing  $\delta$  (0, 0.51, 0.50, 0.75, 0.71, and 1.75 eV for  $\delta = 0$ , 0.33, 0.5, 0.67, 0.83, and 1, respectively) and the band gap of LaNiO<sub>2</sub>H is the largest, as detailed in Figs. 6(a)-6(f). Furthermore, the occupation of the  $3d_{z^2}$  orbital decreases with increasing  $\delta$ , similar to the



FIG. 5. The energy difference and total DOS of three spin configurations in LaNiO<sub>2</sub>H<sub> $\delta$ </sub>. (a) The energy difference between NM, FM, AFM-*C*, and AFM-*G* as a function of H concentration in LaNiO<sub>2</sub>H<sub> $\delta$ </sub>. (b) The total DOS of FM, AFM-*C*, and AFM-*G* in LaNiO<sub>2</sub>, LaNiO<sub>2</sub>H<sub>0.5</sub>, and LaNiO<sub>2</sub>H. The black, green, and red lines represent H concentrations of 0, 0.5, and 1, respectively. The solid and dashed lines represent the majority and minority spin, respectively, as indicated by the direction of the gray arrow. The  $E_F$  is set to zero. Insets are schematics of three magnetic configurations: FM, AFM-*C*, and AFM-*G*.



FIG. 6. The electronic structures under AFM-G configuration. (a)–(f) Unfolded band structures and DOS with orbital projections for LaNiO<sub>2</sub>, LaNiO<sub>2</sub>H<sub>0.33</sub>, LaNiO<sub>2</sub>H<sub>0.5</sub>, LaNiO<sub>2</sub>H<sub>0.67</sub>, LaNiO<sub>2</sub>H<sub>0.83</sub>, and LaNiO<sub>2</sub>H. Only spin-up projected orbitals are shown. The  $E_F$  is set to zero.

NM case. This is due to the repulsive interaction between the energy level of  $3d_{z^2}$  and H-1*s*; the bonding like  $3d_{z^2}$  orbital is pushed away from the  $E_F$  and the antibonding like  $3d_{z^2}$  orbital is pushed above the  $E_F$ . Additionally, the occupation of  $3d_{x^2-y^2}$  in the AFM-*G* state is completely different from that in the NM state:  $3d_{x^2-y^2}$  is almost fully occupied below the  $E_F$  in the AFM-*G* state, while it is partially occupied in the NM state. Besides, the occupation of La 5*d* orbital is insensitive to H. Overall, H doping leads to a metal-to-insulator transition with a critical concentration  $\delta$  of 0.33 and approaches a  $d^9$  insulating state.

# **IV. CONCLUSION**

Using the first-principles calculations in the LaNiO<sub>2</sub>H<sub> $\delta$ </sub> system, we find that H always forms an ordered H-Ni-H chain along the out-of-plane direction due to the strong bonding of Ni- $d_{z^2}$  and H-1s states. In addition, H doping can adjust the band ratio of  $3d_{z^2}$  and  $3d_{x^2-y^2}$  and tune the orbital polarization,

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which may be one reason for the observed superconductivity in a certain H concentration in the experiment. Regarding magnetism properties, there is competition between different magnetic orders. This system is eventually stabilized to the AFM-*G* ground state with increasing H concentration, with the presence of strong antiferromagnetic interactions. As the H concentration increases, a metal-to-insulator transition occurs in the AFM state. These results suggest that H may play an important role in the fundamental electronic structure of LaNiO<sub>2</sub>H<sub> $\delta$ </sub>, and our work may also potentially contribute to the understanding of infinite-layer nickelates superconductivity.

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